

Thomas Schäfers

List of Publications by Year in descending order

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212
papers

4,449
citations

125106

35
h-index

162838

57
g-index

223
all docs

223
docs citations

223
times ranked

3889
citing authors

#	ARTICLE	IF	CITATIONS
1	Te-doped selective-area grown InAs nanowires for superconducting hybrid devices. Physical Review Materials, 2022, 6, .	0.9	1
2	Gate-induced decoupling of surface and bulk state properties in selectively-deposited Bi ₂ Te ₃ nanoribbons. SciPost Physics Core, 2022, 5, .	0.9	8
3	Investigation of Peculiarities of Coherent Magnetotransport of InN Nanowires Using Scanning Gate Microscopy. Journal of Experimental and Theoretical Physics, 2022, 134, 95-102.	0.2	1
4	Fully <i>in situ</i> Nb/InAs-nanowire Josephson junctions by selective-area growth and shadow evaporation. Nanoscale Advances, 2021, 3, 1413-1421.	2.2	11
5	Flux periodic oscillations and phase-coherent transport in GeTe nanowire-based devices. Nature Communications, 2021, 12, 754.	5.8	6
6	Reappearance of first Shapiro step in narrow topological Josephson junctions. Science Advances, 2021, 7, .	4.7	14
7	In-plane magnetic field-driven symmetry breaking in topological insulator-based three-terminal junctions. Communications Materials, 2021, 2, .	2.9	5
8	Quantum Transport in Topological Surface States of Selectively Grown Bi ₂ Te ₃ Nanoribbons. Advanced Electronic Materials, 2020, 6, 2000205.	2.6	21
9	Exfoliated hexagonal BN as gate dielectric for InSb nanowire quantum dots with improved gate hysteresis and charge noise. Applied Physics Letters, 2020, 116, 253101.	1.5	4
10	Hard-Gap Spectroscopy in a Self-Defined Mesoscopic InAs Nanowire Josephson Junction. Physical Review Applied, 2020, 14, .	1.5	4
11	Proximity-Induced Superconductivity in Nb/Sb ₂ Te ₃ Nanoribbon/Nb Junctions. Annalen Der Physik, 2020, 532, 2000273.	0.9	5
12	Phase-coherent loops in selectively-grown topological insulator nanoribbons. Nanotechnology, 2020, 31, 325001.	1.3	12
13	Phase coherent transport and spin-orbit interaction in GaAs/InSb core/shell nanowires. Semiconductor Science and Technology, 2020, 35, 085003.	1.0	5
14	Selective area growth and stencil lithography for in situ fabricated quantum devices. Nature Nanotechnology, 2019, 14, 825-831.	15.6	70
15	Exploiting topological matter for Majorana physics and devices. Solid-State Electronics, 2019, 155, 99-104.	0.8	8
16	Signatures of induced superconductivity in AlOx-capped topological heterostructures. Solid-State Electronics, 2019, 155, 111-116.	0.8	4
17	Dresselhaus spin-orbit coupling in [111]-oriented semiconductor nanowires. Physical Review B, 2019, 99, .	1.1	7
18	Towards semiconductor-superconductor hybrid qubits based on InAs/Al core/shell nanowires. , 2019, , .		0

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19	Visualization and investigation of the non-thermalized electrons in an InAs nanowire by scanning gate microscopy. <i>Journal of Physics Condensed Matter</i> , 2019, 31, 415302.	0.7	1
20	Phase-coherent transport in selectively grown topological insulator nanodots. <i>Nanotechnology</i> , 2019, 30, 055201.	1.3	6
21	Quantum interferometer based on GaAs/InAs core/shell nanowires connected to superconducting contacts. <i>Semiconductor Science and Technology</i> , 2018, 33, 064001.	1.0	4
22	Magnetotransport signatures of three-dimensional topological insulator nanostructures. <i>Physical Review B</i> , 2018, 97, .	1.1	18
23	Phase-coherent transport in topological insulator nanocolumns and nanoribbons. , 2018, , .		2
24	Magnetoresistance oscillations in MBE-grown Sb ₂ Te ₃ thin films. <i>Applied Physics Letters</i> , 2017, 110, .	1.5	13
25	Stencil lithography of superconducting contacts on MBE-grown topological insulator thin films. <i>Journal of Crystal Growth</i> , 2017, 477, 183-187.	0.7	13
26	Signatures of interaction-induced helical gaps in nanowire quantum point contacts. <i>Nature Physics</i> , 2017, 13, 563-567.	6.5	77
27	Electron Interference in Hall Effect Measurements on GaAs/InAs Core/Shell Nanowires. <i>Nano Letters</i> , 2017, 17, 128-135.	4.5	10
28	MBE growth of Al/InAs and Nb/InAs superconducting hybrid nanowire structures. <i>Nanoscale</i> , 2017, 9, 16735-16741.	2.8	22
29	Electrical properties of lightly Ga-doped ZnO nanowires. <i>Semiconductor Science and Technology</i> , 2017, 32, 125010.	1.0	8
30	Nano-Angle Resolved Photoemission Spectroscopy on Topological insulator Sb ₂ Te ₃ nanowires responsible of quantum transport. <i>Journal of Physics: Conference Series</i> , 2017, 864, 012041.	0.3	3
31	Anisotropic phase coherence in GaAs/InAs core/shell nanowires. <i>Nanotechnology</i> , 2017, 28, 445202.	1.3	3
32	Magnetoconductance correction in zinc-blende semiconductor nanowires with spin-orbit coupling. <i>Physical Review B</i> , 2017, 96, .	1.1	10
33	Strain relaxation and ambipolar electrical transport in GaAs/InSb core-shell nanowires. <i>Nanoscale</i> , 2017, 9, 18392-18401.	2.8	10
34	Stability of charged density waves in InAs nanowires in an external magnetic field. <i>Journal of Physics Condensed Matter</i> , 2017, 29, 475601.	0.7	2
35	Experimental determination of Rashba and Dresselhaus parameters and g^* -factor anisotropy via Shubnikov-de Haas oscillations. <i>New Journal of Physics</i> , 2017, 19, 103012.	1.2	13
36	Schmalbuch et al. Reply:. <i>Physical Review Letters</i> , 2016, 117, 139702.	2.9	0

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37	Electronic Properties of Complex Self-Assembled InAs Nanowire Networks. <i>Advanced Electronic Materials</i> , 2016, 2, 1500460.	2.6	10
38	Ballistic and spin transport in InAs nanowires. , 2016, , .		0
39	Confinement and inhomogeneous broadening effects in the quantum oscillatory magnetization of quantum dot ensembles. <i>Journal of Physics Condensed Matter</i> , 2016, 28, 045301.	0.7	3
40	Quantum Transport and Nano Angle-resolved Photoemission Spectroscopy on the Topological Surface States of Single Sb ₂ Te ₃ Nanowires. <i>Scientific Reports</i> , 2016, 6, 29493.	1.6	43
41	Ballistic Transport and Exchange Interaction in InAs Nanowire Quantum Point Contacts. <i>Nano Letters</i> , 2016, 16, 3116-3123.	4.5	46
42	Spintronics with semiconductor nanowires. , 2016, , .		0
43	Impact of Tunnel-Barrier Strength on Magnetoresistance in Carbon Nanotubes. <i>Physical Review Applied</i> , 2016, 5, .	1.5	6
44	Weak (anti)localization in tubular semiconductor nanowires with spin-orbit coupling. <i>Physical Review B</i> , 2016, 93, .	1.1	24
45	Adiabatic Edge Channel Transport in a Nanowire Quantum Point Contact Register. <i>Nano Letters</i> , 2016, 16, 4569-4575.	4.5	24
46	Structural and electrical properties of GaAs/InSb core-shell nanowires. , 2016, , .		1
47	Growth, characterization, and transport properties of ternary (Bi _x Sb _{1-x}) ₂ Te ₃ topological insulator layers. <i>Journal of Physics Condensed Matter</i> , 2016, 28, 495501.	0.7	41
48	Angle-dependent magnetotransport in GaAs/InAs core/shell nanowires. <i>Scientific Reports</i> , 2016, 6, 24573.	1.6	10
49	Selective area growth of Bi ₂ Te ₃ and Sb ₂ Te ₃ topological insulator thin films. <i>Journal of Crystal Growth</i> , 2016, 443, 38-42.	0.7	32
50	P _N Junctions in Ultrathin Topological Insulator Sb ₂ Te ₃ /Bi ₂ Te ₃ Heterostructures Grown by Molecular Beam Epitaxy. <i>Crystal Growth and Design</i> , 2016, 16, 2057-2061.	1.4	36
51	Crystal Phase Transformation in Self-Assembled InAs Nanowire Junctions on Patterned Si Substrates. <i>Nano Letters</i> , 2016, 16, 1933-1941.	4.5	26
52	Correlations of the mutual positions of the nodes of charge density waves in side-by-side placed InAs wires measured with scanning gate microscopy. <i>JETP Letters</i> , 2015, 101, 628-632.	0.4	4
53	Micromechanical measurement of beating patterns in the quantum oscillatory chemical potential of InGaAs quantum wells due to spin-orbit coupling. <i>Applied Physics Letters</i> , 2015, 107, 092101.	1.5	2
54	Realization of a vertical topological p _n junction in epitaxial Sb ₂ Te ₃ /Bi ₂ Te ₃ heterostructures. <i>Nature Communications</i> , 2015, 6, 8816.	5.8	85

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55	Simultaneous Integration of Different Nanowires on Single Textured Si (100) Substrates. Nano Letters, 2015, 15, 1979-1986.	4.5	8
56	Micro-pixel light emitting diodes: Impact of the chip process on microscopic electro- and photoluminescence. Applied Physics Letters, 2015, 106, .	1.5	17
57	Resolving ambiguities in nanowire field-effect transistor characterization. Nanoscale, 2015, 7, 18188-18197.	2.8	29
58	Investigations of local electronic transport in InAs nanowires by scanning gate microscopy at liquid helium temperatures. JETP Letters, 2014, 100, 32-38.	0.4	7
59	Electron interference and spin transport in nanowire structures. , 2014, , .		0
60	Phase coherent transport in hollow InAs nanowires. Applied Physics Letters, 2014, 105, 113111.	1.5	6
61	Flux periodic magnetoconductance oscillations in GaAs/InAs core/shell nanowires. Physical Review B, 2014, 89, .	1.1	47
62	Spin injection and spin-orbit coupling in low-dimensional semiconductor nanostructures. , 2014, , .		0
63	Quantum dots in InAs nanowires induced by surface potential fluctuations. Nanotechnology, 2014, 25, 135203.	1.3	7
64	The electronic transport of top subband and disordered sea in an InAs nanowire in the presence of a mobile gate. Journal of Physics Condensed Matter, 2014, 26, 165304.	0.7	8
65	Amphoteric Nature of Sn in CdS Nanowires. Nano Letters, 2014, 14, 518-523.	4.5	32
66	Giant Magnetoconductance Oscillations in Hybrid Superconductor~Semiconductor Core/Shell Nanowire Devices. Nano Letters, 2014, 14, 6269-6274.	4.5	17
67	Crystal Phase Selective Growth in GaAs/InAs Core~Shell Nanowires. Crystal Growth and Design, 2014, 14, 1167-1174.	1.4	27
68	Crossover from Josephson Effect to Single Interface Andreev Reflection in Asymmetric Superconductor/Nanowire Junctions. Nano Letters, 2014, 14, 4977-4981.	4.5	24
69	Self-catalyzed VLS grown InAs nanowires with twinning superlattices. Nanotechnology, 2013, 24, 335601.	1.3	56
70	Frequency anomaly in the Rashba-effect induced magnetization oscillations of a high-mobility two-dimensional electron system. Physical Review B, 2013, 87, .	1.1	10
71	Controlled wurtzite inclusions in self-catalyzed zinc blende III~V semiconductor nanowires. Journal of Crystal Growth, 2013, 378, 506-510.	0.7	30
72	Nanoimprint and selective-area MOVPE for growth of GaAs/InAs core/shell nanowires. Nanotechnology, 2013, 24, 085603.	1.3	45

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73	Distortions of the coulomb blockade conductance line in scanning gate measurements of InAs nanowire based quantum dots. Journal of Experimental and Theoretical Physics, 2013, 116, 138-144.	0.2	6
74	Gate-induced transition between metal-type and thermally activated transport in self-catalyzed MBE-grown InAs nanowires. Nanotechnology, 2013, 24, 325201.	1.3	4
75	The absence of Fraunhofer patterns in narrow Nb/InAs-nanowire/Nb junctions. , 2013, , .		1
76	Realization of nanoscaled tubular conductors by means of GaAs/InAs core/shell nanowires. Nanotechnology, 2013, 24, 035203.	1.3	43
77	FLUX QUANTUM OSCILLATIONS IN GaAs/InAs CORE/SHELL NANOWIRES. , 2013, , .		0
78	Scanning tunneling microscopy with InAs nanowire tips. Applied Physics Letters, 2012, 101, .	1.5	5
79	Monitoring structural influences on quantum transport in InAs nanowires. Applied Physics Letters, 2012, 101, 062104.	1.5	5
80	Supercurrent in Nb/InAs-nanowire/Nb Josephson junctions. Journal of Applied Physics, 2012, 112, .	1.1	43
81	Phase coherent transport in InSb nanowires. Applied Physics Letters, 2012, 101, 082103.	1.5	15
82	Preparation of Ohmic contacts to GaAs/AlGaAs-core/shell-nanowires. Applied Physics Letters, 2012, 100, .	1.5	16
83	Electrical Spin Injection into InN Semiconductor Nanowires. Nano Letters, 2012, 12, 4437-4443.	4.5	36
84	Direct observation of standing electron waves in diffusively conducting InAs nanowire. JETP Letters, 2012, 96, 109-112.	0.4	5
85	Hall effect measurements on InAs nanowires. Applied Physics Letters, 2012, 101, 152106.	1.5	88
86	Negative differential conductance in InAs wire based double quantum dot induced by a charged AFM tip. Journal of Experimental and Theoretical Physics, 2012, 115, 1062-1067.	0.2	4
87	Molecular Beam Epitaxy Growth of GaAs/InAs Core-Shell Nanowires and Fabrication of InAs Nanotubes. Nano Letters, 2012, 12, 5559-5564.	4.5	71
88	Comparison of InAs nanowire conductivity: influence of growth method and structure. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 230-234.	0.8	8
89	Electronic Transport with Dielectric Confinement in Degenerate InN Nanowires. Nano Letters, 2012, 12, 2768-2772.	4.5	23
90	Field effect transistor based on single crystalline InSb nanowire. Journal of Materials Chemistry, 2011, 21, 2459.	6.7	54

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91	Manipulating InAs nanowires with submicrometer precision. Review of Scientific Instruments, 2011, 82, 113705.	0.6	30
92	Effect of Si-doping on InAs nanowire transport and morphology. Journal of Applied Physics, 2011, 110, .	1.1	61
93	Investigation of the surface properties of gold nanowire arrays. Applied Surface Science, 2011, 258, 147-150.	3.1	7
94	Electronic Phase Coherence in InAs Nanowires. Nano Letters, 2011, 11, 3550-3556.	4.5	68
95	Spin precession and modulation in ballistic cylindrical nanowires due to the Rashba effect. Physical Review B, 2011, 83, .	1.1	45
96	Low-temperature conductance of the weak junction in InAs nanowire in the field of AFM scanning gate. JETP Letters, 2011, 93, 10-14.	0.4	10
97	New method of creation of a rearrangeable local Coulomb potential profile and its application for investigations of local conductivity of InAs nanowires. Physica E: Low-Dimensional Systems and Nanostructures, 2011, 44, 690-695.	1.3	5
98	Optical and electrical properties of gold nanowires synthesized by electrochemical deposition. Journal of Applied Physics, 2011, 110, 094301.	1.1	15
99	Improved gate-control in InAs nanowire structures by $\text{Al}_2\text{O}_3/\text{GdScO}_3$ as a gate dielectric. Applied Physics A: Materials Science and Processing, 2010, 100, 305-308.	1.1	2
100	Strain-enhanced electron mobility anisotropy in $\text{In}_x\text{Ga}_{1-x}\text{As}/\text{InP}$ two-dimensional electron gases. Physica E: Low-Dimensional Systems and Nanostructures, 2010, 42, 1130-1133.	1.3	5
101	Quantum transport in narrow-gap semiconductor nanocolumns. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 386-389.	0.8	5
102	Two-Dimensional Optical Control of Electron Spin Orientation by Linearly Polarized Light in InGaAs. Physical Review Letters, 2010, 105, 246603.	2.9	11
103	Universal conductance fluctuations and localization effects in InN nanowires connected in parallel. Journal of Applied Physics, 2010, 108, .	1.1	20
104	Josephson supercurrent in Nb/InN-nanowire/Nb junctions. Applied Physics Letters, 2010, 96, 132504.	1.5	29
105	LaLuO_3 as a high- κ gate dielectric for InAs nanowire structures. Semiconductor Science and Technology, 2010, 25, 085001.	1.0	5
106	Quantum phenomena during electron transport in InAs nanowires. , 2010, , .		0
107	Spin-orbit coupling and phase coherence in InAs nanowires. Physical Review B, 2010, 82, .	1.1	79
108	Spin-orbit coupling and phase-coherent transport in InN nanowires. Physical Review B, 2009, 80, .	1.1	24

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109	Origin and limiting mechanism of induced nonequilibrium currents in gated two-dimensional electron systems. Physical Review B, 2009, 80, .	1.1	11
110	Phase-coherence and symmetry in four-terminal magnetotransport measurements on InN nanowires. Applied Physics Letters, 2009, 94, 252107.	1.5	14
111	Measurement of effective electron mass in biaxial tensile strained silicon on insulator. Applied Physics Letters, 2009, 95, .	1.5	25
112	Electrical transport properties of single undoped and n-type doped InN nanowires. Nanotechnology, 2009, 20, 405206.	1.3	46
113	Spin-orbit coupling in Ga _x In _{1-x} As/InP two-dimensional electron gases and quantum wire structures. Semiconductor Science and Technology, 2009, 24, 064001.	1.0	13
114	Low Frequency Noise in 2 DEG Channel of AlGa _N GaN Heterostructures Scaled to Nanosize Width. , 2009, , .		1
115	Study on growth and electrical performance of double-heterostructure AlGa _N /Ga _N /AlGa _N field-effect transistors. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S1003.	0.8	6
116	Influence of barrier thickness on AlInN/AlN/GaN heterostructures and device properties. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S1041.	0.8	13
117	Influence of growth temperature on the selective area MOVPE of InAs nanowires on GaAs (111) B using N ₂ carrier gas. Journal of Crystal Growth, 2009, 311, 3813-3816.	0.7	36
118	Influence of growth temperature on GaN:Cr incorporation and structural properties in MOVPE. Journal of Crystal Growth, 2009, 312, 1-9.	0.7	9
119	In _x Ga _{1-x} As/InP selective area metal-organic vapor phase epitaxy for non-magnetic semiconductor spintronics. Journal of Crystal Growth, 2008, 310, 4821-4825.	0.7	2
120	Flux Quantization Effects in InN Nanowires. Nano Letters, 2008, 8, 2834-2838.	4.5	69
121	Phase-coherent transport in InN nanowires of various sizes. Physical Review B, 2008, 77, .	1.1	27
122	Temperature dependence of the phase-coherence length in InN nanowires. Applied Physics Letters, 2008, 92, .	1.5	29
123	Spin-splitting analysis of a two-dimensional electron gas in almost strain-free $\text{In}_x\text{Ga}_{1-x}\text{As}/\text{InP}$ two-dimensional electron gas. Physical Review B, 2008, 77, .	1.1	25
124	Suppression of weak antilocalization in an $\text{Al}_x\text{Ga}_{1-x}\text{N}/\text{GaN}$ two-dimensional electron gas by an in-plane magnetic field. Physical Review B, 2007, 75, .	1.1	7
125	Spin-splitting and strongly enhanced magnetoresistance oscillations in $\text{In}_x\text{Ga}_{1-x}\text{As}/\text{InP}$ two-dimensional electron gas. Physical Review B, 2007, 75, .	1.1	26
126	Zeeman splitting in ballistic GaInAs _N InP split-gate quantum point contacts. Applied Physics Letters, 2007, 90, 122107.	1.5	14

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127	Weak antilocalization in high mobility $\text{Al}_x\text{Ga}_{1-x}\text{As}/\text{InP}$ narrow quantum wires. Applied Physics Letters, 2006, 88, 032102.	1.1	14
128	Spin-splitting characterization of an InGaSb 2DEC by using magnetoresistance measurements with tilted magnetic fields. AIP Conference Proceedings, 2007, , .	0.3	0
130	The growth of Cr-doped GaN by MOVPE towards spintronic applications. Physica Status Solidi (A) Applications and Materials Science, 2007, 204, 72-77.	0.8	4
131	Rashba effect in $\text{GaIn}_{1-x}\text{As}/\text{InP}$ quantum wire structures. Applied Physics A: Materials Science and Processing, 2007, 87, 577-584.	1.1	10
132	Weak antilocalization in a polarization-doped $\text{Al}_x\text{Ga}_{1-x}\text{N}/\text{GaN}$ heterostructure with single subband occupation. Applied Physics Letters, 2006, 88, 022111.	1.5	52
133	Spin-orbit coupling in gated AlGaIn/GaN 2-dimensional electron gases. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 4247-4250.	0.8	3
134	Weak antilocalization measurements on a 2-dimensional electron gas in an $\text{InGaSb}/\text{InAlSb}$ heterostructure. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 4227-4230.	0.8	11
135	Effect of confinement on the weak antilocalization in InGaAs/InP quasi-1D structures. Physica E: Low-Dimensional Systems and Nanostructures, 2006, 32, 333-336.	1.3	1
136	Weak antilocalization in gate-controlled $\text{Al}_x\text{Ga}_{1-x}\text{N}/\text{GaN}$ two-dimensional electron gases. Physical Review B, 2006, 73, .	1.1	51
137	Rashba effect in InGaAs/InP parallel quantum wires. Applied Physics Letters, 2006, 88, 032102.	1.5	30
138	Suppression of weak antilocalization in $\text{GaIn}_{1-x}\text{As}/\text{InP}$ narrow quantum wires. Physical Review B, 2006, 74, .	1.1	66
139	Localized electrochemical oxidation of thin Nb Films in microscopic and nanoscopic dimensions. Surface Science, 2005, 597, 173-180.	0.8	10
140	Principles of electrochemical nanotechnology and their application for materials and systems. Electrochimica Acta, 2005, 51, 775-786.	2.6	13
141	Epitaxial growth of Fe on GaN(0001): structural and magnetic properties. Physica Status Solidi (A) Applications and Materials Science, 2005, 202, 754-757.	0.8	13
142	Longitudinal photocurrent spectroscopy of a single GaAs/AlGaAs v-groove quantum wire. Nanotechnology, 2005, 16, 307-311.	1.3	3
143	Shot noise of large charge quanta in superconductor/semiconductor/superconductor junctions. Physical Review B, 2005, 71, .	1.1	6
144	Weak Antilocalization in Polarization-Doped AlGaIn/GaN Heterostructures. Materials Research Society Symposia Proceedings, 2005, 892, 370.	0.1	0

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145	Magnetosubbands of semiconductor quantum wires with Rashba spin-orbit coupling. Physical Review B, 2005, 71, .	1.1	50
146	Effect of Rashba spin-orbit coupling on magnetotransport in InGaAs/InP quantum wire structures. Physical Review B, 2004, 69, .	1.1	74
147	Andreev reflection and enhanced subgap conductance in NbN/Au/InGaAs/InP junctions. Journal of Applied Physics, 2004, 96, 3366-3370.	1.1	16
148	Magnetic and structural properties of GaN thin layers implanted with Mn, Cr, or V ions. Journal of Applied Physics, 2004, 96, 5663-5667.	1.1	18
149	Rashba spin-orbit coupling in InGaAs/InP quantum wires. Materials Research Society Symposia Proceedings, 2004, 825, G5.7.1.	0.1	0
150	Rashba effect in gated InGaAs/InP quantum wire structures. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 21, 933-936.	1.3	6
151	Carrier relaxation in GaAs v-groove quantum wires and the effects of localization. Physical Review B, 2004, 70, .	1.1	7
152	Rashba effect in strained InGaAs/InP quantum wire structures. Science and Technology of Advanced Materials, 2003, 4, 19-25.	2.8	13
153	Current-injection in a ballistic multiterminal superconductor/two-dimensional electron gas Josephson junction. Physical Review B, 2003, 67, .	1.1	19
154	Coherent "Metallic" Resistance and Medium Localization in a Disordered One-Dimensional Insulator. Physical Review Letters, 2003, 91, 136803.	2.9	13
155	Control of interference effects in a two-dimensional-electron-gas/superconductor junction by the Josephson effect. Physical Review B, 2003, 67, .	1.1	2
156	Coherent resistance of a disordered one-dimensional wire: Expressions for all moments and evidence for non-Gaussian distribution. Physical Review B, 2003, 67, .	1.1	6
157	Supercurrent control in a multi-terminal Nb-InGaAs/InP junction with Nb injector electrodes. Superconductor Science and Technology, 2003, 16, 714-719.	1.8	1
158	CARRIER INJECTION FROM SUPERCONDUCTING ELECTRODES INTO A NB-INGAAS/INP JOSEPHSON JUNCTION. , 2003, , .		0
159	Investigation of Ferromagnetic Microstructures by Local Hall Effect and Magnetic Force Microscopy. Japanese Journal of Applied Physics, 2002, 41, 2497-2500.	0.8	10
160	Optical measurements of carrier relaxation and transport in single GaAs v-groove quantum wire structures. Physica B: Condensed Matter, 2002, 314, 413-416.	1.3	5
161	Dephasing of coherent one-dimensional transport in a disordered wire. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 12, 703-707.	1.3	0
162	2D "1D crossover from quantum well to quantum wire behaviour in GaAs v-groove structures. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 13, 174-177.	1.3	2

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163	Model for ballistic spin-transport in ferromagnet/two-dimensional electron gas/ferromagnet structures. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2002, 13, 564-567.	1.3	4
164	Interference ferromagnet/semiconductor/ferromagnet spin field-effect transistor. <i>Physical Review B</i> , 2001, 64, .	1.1	53
165	Carrier transport in multi-terminal superconductor/two-dimensional electron gas Josephson junctions. <i>Physica C: Superconductivity and Its Applications</i> , 2001, 352, 144-148.	0.6	1
166	Control of Aharonov-Bohm oscillations in a AlGaAs/GaAs ring by asymmetric and symmetric gate biasing. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2001, 9, 635-641.	1.3	13
167	Superconductor/Semiconductor Junctions. <i>Springer Tracts in Modern Physics</i> , 2001, , .	0.1	60
168	Enhancement of spin injection from ferromagnetic metal into a two-dimensional electron gas using a tunnel barrier. <i>Physical Review B</i> , 2001, 64, .	1.1	52
169	Scanning Near-Field Optical Spectroscopy of Buried Semiconductor Heterostructures. <i>Springer Proceedings in Physics</i> , 2001, , 703-704.	0.1	3
170	On the choice of precursors for the MOVPE-growth of high-quality Al _{0.30} Ga _{0.70} As/GaAs v-groove quantum wires with large subband spacing. <i>Journal of Crystal Growth</i> , 2000, 221, 91-97.	0.7	9
171	Electron transport in modulation-doped GaAs v-groove quantum wires. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2000, 7, 760-765.	1.3	9
172	Fermi-edge singularities in the photoluminescence and magneto-optical spectra of modulation-doped v-groove quantum wires. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2000, 6, 530-533.	1.3	2
173	Fermi-edge singularities in the photoluminescence spectrum of modulation-doped GaAs v-groove quantum wires. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2000, 7, 517-520.	1.3	2
174	Preparation of transparent Nb/two-dimensional electron gas contacts by using electron cyclotron resonance plasma cleaning. <i>Journal of Applied Physics</i> , 2000, 88, 4440.	1.1	4
175	Splitting of the subgap resistance peak in superconductor/two-dimensional electron gas contacts at high magnetic fields. <i>Physical Review B</i> , 2000, 61, 12463-12466.	1.1	17
176	Adjustment of the critical current in a Nb-In _x Ga _{1-x} As/InP Josephson contact by light exposure. <i>Applied Physics Letters</i> , 1999, 75, 391-393.	1.5	9
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